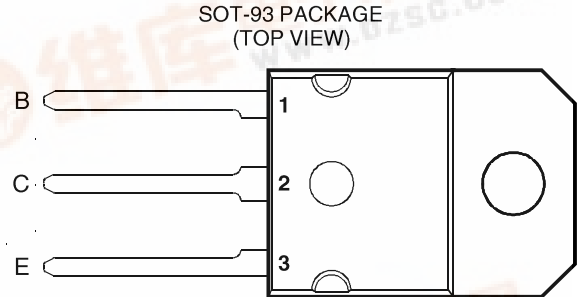


BD246, BD246A, BD246B, BD246C PNP SILICON POWER TRANSISTORS

- Designed for Complementary Use with the BD245 Series
- 80 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- 15 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-emitter voltage ($R_{BE} = 100 \Omega$)	BD246	V_{CER}	-55	V
	BD246A		-70	
	BD246B		-90	
	BD246C		-115	
Collector-emitter voltage ($I_C = -30 \text{ mA}$)	BD246	V_{CEO}	-45	V
	BD246A		-60	
	BD246B		-80	
	BD246C		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-10	A
Peak collector current (see Note 1)		I_{CM}	-15	A
Continuous base current		I_B	-3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	80	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	62.5	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3 \text{ ms}$, duty cycle $\leq 10\%$.

2. Derate linearly to 150°C case temperature at the rate of 0.64 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 24 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20 \text{ mH}$, $I_{B(on)} = -0.4 \text{ A}$, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = -20 \text{ V}$.

BD246, BD246A, BD246B, BD246C PNP SILICON POWER TRANSISTORS

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30$ mA (see Note 5)	$I_B = 0$	BD246 BD246A BD246B BD246C	-45 -60 -80 -100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -55$ V $V_{CE} = -70$ V $V_{CE} = -90$ V $V_{CE} = -115$ V	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	BD246 BD246A BD246B BD246C			-0.4 -0.4 -0.4 -0.4	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30$ V $V_{CE} = -60$ V	$I_B = 0$ $I_B = 0$	BD246/246A BD246B/246C			-0.7 -0.7	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5$ V	$I_C = 0$				-1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -4$ V $V_{CE} = -4$ V $V_{CE} = -4$ V	$I_C = -1$ A $I_C = -3$ A $I_C = -10$ A	(see Notes 5 and 6)	40 20 4			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -0.3$ A $I_B = -2.5$ A	$I_C = -3$ A $I_C = -10$ A	(see Notes 5 and 6)			-1 -4	V
V_{BE} Base-emitter voltage	$V_{CE} = -4$ V $V_{CE} = -4$ V	$I_C = -3$ A $I_C = -10$ A	(see Notes 5 and 6)			-1.6 -3	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = -10$ V	$I_C = -0.5$ A	$f = 1$ kHz	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = -10$ V	$I_C = -0.5$ A	$f = 1$ MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300$ μ s, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.56	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			42	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -1$ A	$I_{B(on)} = -0.1$ A	$I_{B(off)} = 0.1$ A		0.2		μ s
t_{off} Turn-off time	$V_{BE(off)} = 3.7$ V	$R_L = 20$ Ω	$t_p = 20$ μ s, $dc \leq 2\%$		0.8		μ s

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

**BD246, BD246A, BD246B, BD246C
PNP SILICON POWER TRANSISTORS**

TYPICAL CHARACTERISTICS

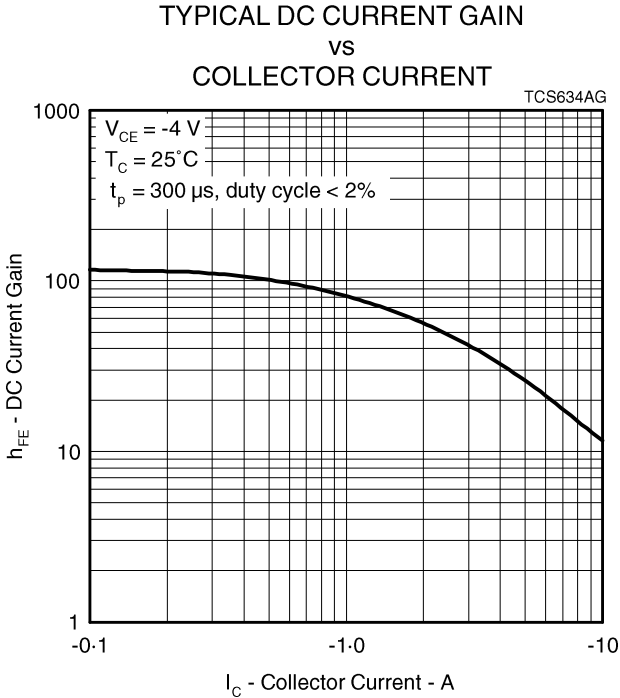


Figure 1.

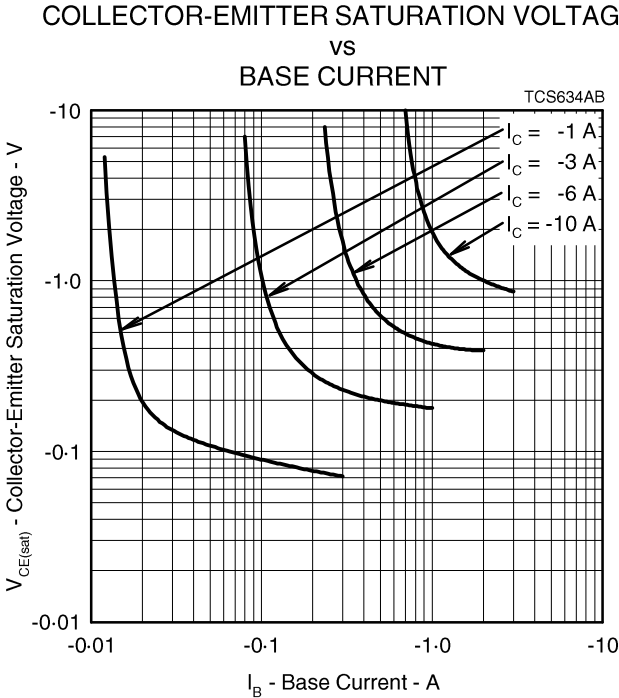


Figure 2.

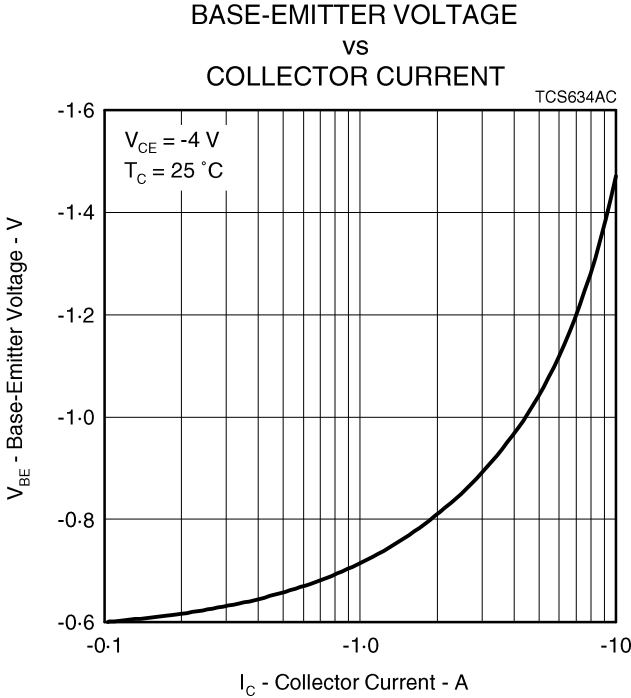


Figure 3.

BD246, BD246A, BD246B, BD246C
PNP SILICON POWER TRANSISTORS

MAXIMUM SAFE OPERATING REGIONS

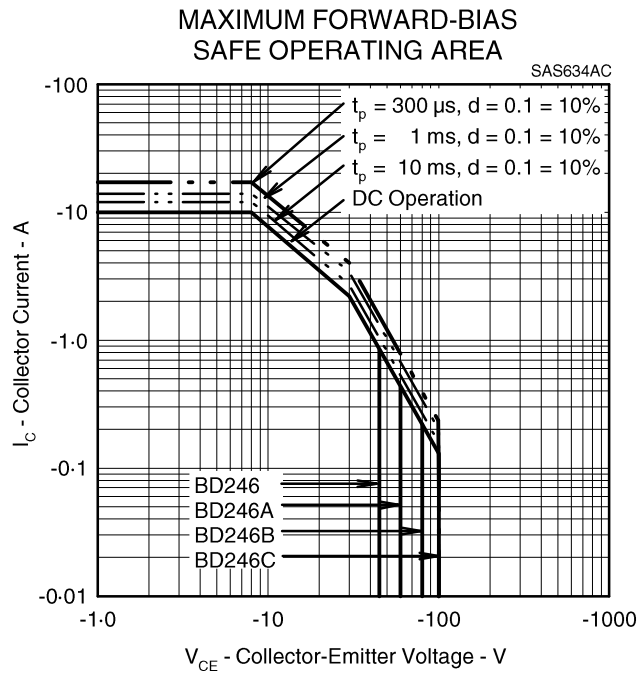


Figure 4.

THERMAL INFORMATION

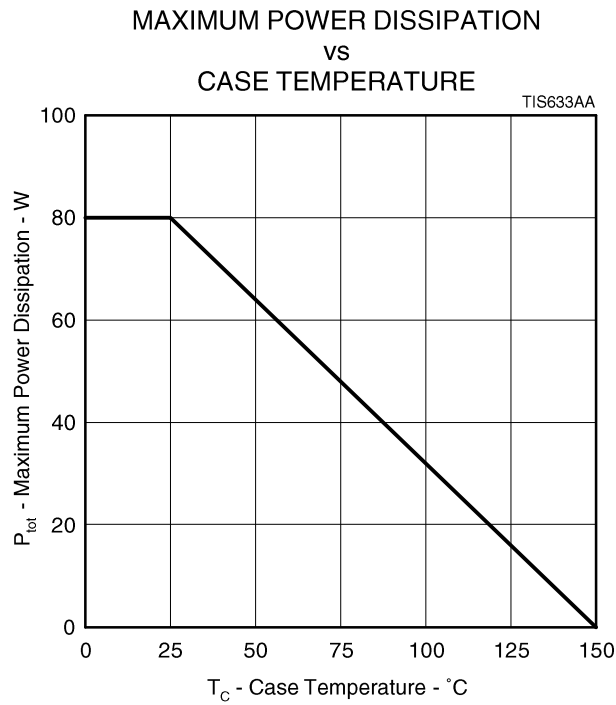


Figure 5.

